

In the Claims:

Claims 1-8 (canceled)

Claim 9 (currently amended): A method of forming an integrated circuit capacitor comprising the steps of:

providing a silicon substrate with a first dielectric film containing at least one copper layer;

forming a etch-stop/barrier layer over said first dielectric layer and said at least one copper layer, wherein said etch-stop/barrier layer contacting contacts said copper layer;

forming a first conductive layer over said first dielectric layer, wherein said first conductive layer contacting contacts said etch-stop/barrier layer; and

removing a region of said first conductive layer such that a portion of said etch-stop/barrier layer remains between said first conductive layer and said copper layer, wherein said first conductive layer, said etch-stop/barrier layer, and said copper layer forming a capacitor.

Claim 10 (previously presented): The method of claim 9 further comprising:

forming copper contacts to said first conductive layer; and

forming a second copper layer that electrically contacts said copper contacts.

Claim 11 (previously presented): The method of claim 9 wherein said first conductive layer is formed from a material selected from the group consisting of aluminum, aluminum oxide, tantalum nitride, titanium nitride, tungsten, tungsten nitride, silicon carbide, and their alloys.

Claim 12 (previously presented): The method of claim 9 wherein said etch-stop/barrier layer is formed using at least two different dielectric films.

Claim 13 (canceled):

Claim 14 (previously presented): The method of claim 9 wherein said etch-stop barrier layer is silicon nitride.

Claims 15-17 (canceled):